



Product Change Notification (PCN)

Date: 25 January 2021

PCN TRACKING NO: PCN# 20210125/SM-2

Subject: Product Change Notification (PCN) for Alliance LPSRAM's (256K)

Description of Change:	Product will only be offered in a non-A Alliance design only
Reason for Change	ZMD wafers production EOL – existing Alliance ‘non-A’ only parts to provide continuous support to ZMD & Alliance’s customers
Traceability, Guidelines (lot, date code, markings, shipment date)	Traceable through marketing part number
Datasheet	Part number changed and relevant datasheets are posted on our website at the following links: https://www.alliancememory.com/products/low-power-asynchronous-sram/
Summary of Alternative between ZMD A parts and Alliance non-A	See table 1 Below

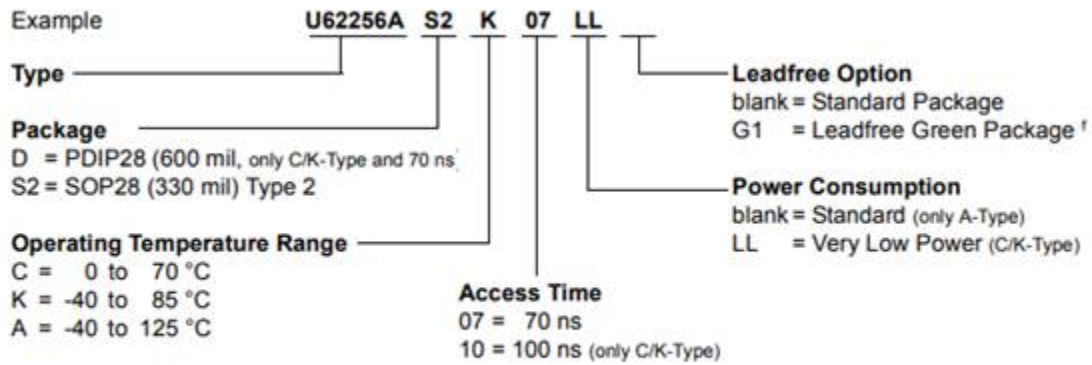
Table 1 – ZMD 256K LPSRAM – EOL

Density	Organization	Alliance/ZMD Part Number	Alliance Alternative Part Number to use
256K	32K x 8	AS6C62256A-70PIN	<u>AS6C62256-55PCN*</u>
256K	32K x 8	AS6C62256A-70PCN	<u>AS6C62256-55PCN</u>
256K	32K x 8	AS6C62256A-70SIN	<u>AS6C62256-55SIN</u>
256K	32K x 8	AS6C62256A-70SINTR	<u>AS6C62256-55SINTR</u>
256K	32K x 8	AS6C62256A-70SCN	<u>AS6C62256-55SCN</u>
256K	32K x 8	AS6C62256A-70SCNTR	<u>AS6C62256-55SCNTR</u>
256K	32K x 8	U62256ADC07LLG1	<u>AS6C62256-55PCN</u>
256K	32K x 8	U62256ADK07LLG1	<u>AS6C62256-55PCN*</u>
256K	32K x 8	U62256AS2C07LLG1	<u>AS6C62256-55SCN</u>
256K	32K x 8	U62256AS2C07LLG1TR	<u>AS6C62256-55SCNTR</u>
256K	32K x 8	U62256AS2K07LLG1	<u>AS6C62256-55SIN</u>
256K	32K x 8	U62256AS2K07LLG1TR	<u>AS6C62256-55SINTR</u>

*Yellow highlights are replacement part with downgraded temp.



ZMD Part Numbering System



† on special request

Last Time Buy Date:	July 25, 2021- corrected to 30 June 2021
Last Time Ship Date:	September 30th, 2021
Sample Availability Date	Existing - Parts already in Production
PCN Effective Date	January 25, 2021

***Any orders after 30 June 2021 are Non-Cancelable/Non-Returnable and cannot be changed. Products cannot be returned in stock rotation after this date.**



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Dear Valued Customer:

This letter provides End-of-Life (EOL) notice of ZMD 256K Low Power SRAM products with a 256K density Organized 32Kx8. These ZMD wafers will move from the original ZMD design to the Alliance design. Please note that the ZMD design and the Alliance design are both fabricated from Global Foundries in Singapore. The assembly (Greatek in Taiwan) and testing (ChipMOS in Taiwan) will remain the same.

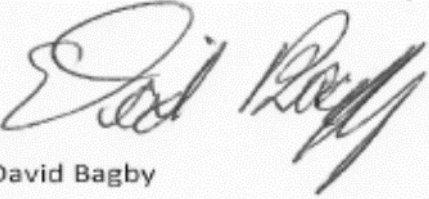
The delivery deadline is **September 30th, 2021** with last time buy (LTB) deadline **on June 30th, 2021**. Please note that the standard shipment dates will apply in general and extended delivery dates must be pre-arranged and accepted in writing by Alliance Memory Management.

Samples are already available for customers to start verification procedures.

We provide product comparisons within the pages that follow this PCN#20210104/SM-2.

Please contact your local Alliance Memory representative if you have any questions regarding this information

Yours faithfully



David Bagby
President
Alliance Memory Inc.



David Bagby
President
Alliance Memory Inc.

AS6C62256A-70PIN & U62256ADK07LLG1 & AS6C62256-55PCN Comparison

Part Number & result Parameter	AS6C62256A- 70PIN	U62256ADK07LLG1	AS6C62256-55PCN	Comments
Product Description	Low Power ASRAM	Low Power ASRAM	Low Power ASRAM	
Capacity	256Kb	256Kb	256Kb	Same
Memory Orgn.	32K x 8bits	32K x 8bits	32K x 8bits	Same
Oper. Power Supply	V _{CC} =4.5V ~ 5.5V	V _{CC} =4.5V ~ 5.5V	V _{CC} =2.7V ~ 5.5V	AS6C62256-55PCN better
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Commercial (0°C to 70°C)	Different
I/O Capacitance	CIO: 7pf (Max.)	CIO: 7pf (Max.)	CIO: 8pf (Max.)	Comparable
Read Cycle Time (tRC)	70ns (Min.)	70ns (Min.)	55ns (Min.)	AS6C62256-55PCN better
WriteCycleTime(tWC)	70ns (Min.)	70ns (Min.)	55ns (Min.)	AS6C62256-55PCN better
AddrAccessTime(tAA)	70ns (Max.)	70ns (Max.)	55ns (Max.)	AS6C62256-55PCN better
OE Access Time (tOE)	35ns (Max.)	35ns (Max.)	30ns (Max.)	Comparable
V_{OH}(V) @ -1.0mA	2.4 (Min.)	2.4 (Min.)	2.4 (Min.)	Same
V_{OL}(V)	0.4 (Max.)	0.4 (Max.)	0.4 (Max.)	Same
V_{IH}(V)	2.2 (Min.)	2.2 (Min.)	2.4 (Min.)	Comparable
V_{IL}(V)	0.8 (Max.)	0.6 (Max.)	0.6 (Max.)	Comparable
I_{LI} / I_{LO}(uA)	2 (Max.)	2 (Max.)	1 (Max.)	Comparable
Oper. Current	ICC = 70mA(Max.)	ICC = 70mA(Max.)	ICC = 45mA(Max.)	AS6C62256-55PCN better
Standby Current ISB1(CMOS level)	10uA (Max.)	10uA (Max.)	30uA (Max.)	Different
Standby Current ISB2(TTL level)	1mA (Max.)	1mA (Max.)	3mA	Different
V_{DR}	2 (Min.)	2V (Min.)	1.5V (Min.)	AS6C62256-55PCN better
Package Dim	28Pin 600mil PDIP	28Pin 600mil PDIP	28Pin 600mil PDIP	Same
Package Material	Pb and Halogen Free	Pb and Halogen Free	Pb and Halogen Free	Same
Pin to Pin Compatible	Yes	Yes	Yes	Same



AS6C62256A-70SCN & U62256AS2C07LLG1 & AS6C62256-55SCN Comparison

Part Number & result Parameter	AS6C62256A-70SCN	U62256AS2C07LLG1	AS6C62256-55SCN	Comments
Product Description	Low Power ASRAM	Low Power ASRAM	Low Power ASRAM	
Capacity	256Kb	256Kb	256Kb	Same
Memory Organization	32K x 8bits	32K x 8bits	32K x 8bits	Same
Oper. Power Supply	V _{CC} =4.5V ~ 5.5V	V _{CC} =4.5V ~ 5.5V	V _{CC} =2.7V ~ 5.5V	AS6C62256-55SCN better
Operating Temperature	Commercial (0°C to 70°C)	Commercial (0°C to 70°C)	Commercial (0°C to 70°C)	Same
I/O Capacitance	CIO: 7pf (Max.)	CIO: 7pf (Max.)	CIO: 8pf (Max.)	Comparable
Read Cycle Time (tRC)	70ns (Min.)	70ns (Min.)	55ns (Min.)	AS6C62256-55SCN better
WriteCycleTime(tWC)	70ns (Min.)	70ns (Min.)	55ns (Min.)	AS6C62256-55SCN better
AddrAccessTime(tAA)	70ns (Max.)	70ns (Max.)	55ns (Max.)	AS6C62256-55SCN better
OE Access Time (tOE)	35ns (Max.)	35ns (Max.)	30ns (Max.)	Comparable
V_{OH}(V)	2.4 (Min.)	2.4 (Min.)	2.4 (Min.)	Same
V_{OL}(V)	0.4 (Max.)	0.4 (Max.)	0.4 (Max.)	Same
V_{IH}(V)	2.2 (Min.)	2.2 (Min.)	2.4 (Min.)	Comparable
V_{IL}(V)	0.8 (Max.)	0.6 (Max.)	0.6 (Max.)	Comparable
I_{LI} / I_{LO}(uA)	2 (Max.)	2 (Max.)	1 (Max.)	Same
Oper. Current	ICC = 70mA(Max.)	ICC = 70mA(Max.)	ICC = 45mA(Max.)	AS6C62256-55SCN better
Standby Current ISB1(CMOS level)	10uA (Max.)	5uA (Max.)	15uA (Max.)	Comparable
Standby Current ISB2(TTL level)	1mA (Max.)	1mA (Max.)	3mA	Different
V_{DR}	2 (Min.)	2V (Min.)	1.5V (Min.)	AS6C62256-55SCN better
Package Dim	330mil SOP28	330mil SOP28	330mil SOP28	Same
Package Material	Pb and Halogen Free	Pb and Halogen Free	Pb and Halogen Free	Same
Pin to Pin Compatible	Yes	Yes	Yes	Same



AS6C62256A-70SIN & U62256AS2K07LLG1 & AS6C62256-55SIN Comparison

Part Number & result Parameter	AS6C62256A-70SIN	U62256AS2K07LLG1	AS6C62256-55SIN	Comments
Product Description	Low Power ASRAM	Low Power ASRAM	Low Power ASRAM	
Capacity	256Kb	256Kb	256Kb	Same
Memory Organization	32K x 8bits	32K x 8bits	32K x 8bits	Same
Oper. Power Supply	V _{CC} =4.5V ~ 5.5V	V _{CC} =4.5V ~ 5.5V	V _{CC} =2.7V ~ 5.5V	AS6C62256-55SIN better
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Same
I/O Capacitance	CIO: 7pf (Max.)	CIO: 7pf (Max.)	CIO: 8pf (Max.)	Comparable
Read Cycle Time (tRC)	70ns (Min.)	70ns (Min.)	55ns (Min.)	AS6C62256-55SIN better
Write Cycle Time (tWC)	70ns (Min.)	70ns (Min.)	55ns (Min.)	AS6C62256-55SIN better
Addr Access Time (tAA)	70ns (Max.)	70ns (Max.)	55ns (Max.)	AS6C62256-55SIN better
OE Access Time (tOE)	35ns (Max.)	35ns (Max.)	30ns (Max.)	Comparable
V_{OH}(V)	2.4 (Min.)	2.4 (Min.)	2.4 (Min.)	Same
V_{OL}(V)	0.4 (Max.)	0.4 (Max.)	0.4 (Max.)	Same
V_{IH}(V)	2.2 (Min.)	2.2 (Min.)	2.4 (Min.)	Same
V_{IL}(V)	0.8 (Max.)	0.6 (Max.)	0.6 (Max.)	Same
I_{LI} / I_{LO}(uA)	2 (Max.)	2 (Max.)	1 (Max.)	Comparable
Oper. Current	ICC = 70mA(Max.)	ICC = 70mA(Max.)	ICC = 45mA(Max.)	AS6C62256-55SIN better
Standby Current ISB1(CMOS level)	10uA (Max.)	10uA (Max.)	30uA (Max.)	Comparable
Standby Current ISB2(TTL level)	1mA (Max.)	1mA (Max.)	3mA	Different
V_{DR}	2 (Min.)	2V (Min.)	1.5V (Min.)	AS6C62256-55SIN better
Package Dim	330mil SOP28	330mil SOP28	330mil SOP28	Same
Package Material	Pb and Halogen Free	Pb and Halogen Free	Pb and Halogen Free	Same
Pin to Pin Compatible	Yes	Yes	Yes	Same



AS6C62256A-70PCN & U62256ADC07LLG1 &AS6C62256-55PCN Comparison

Part Number & result Parameter	AS6C62256A-70PCN	U62256ADC07LLG1	AS6C62256-55PCN	Comments
Product Description	Low Power ASRAM	Low Power ASRAM	Low Power ASRAM	
Capacity	256Kb	256Kb	256Kb	Same
Memory Organization	32K x 8bits	32K x 8bits	32K x 8bits	Same
Oper. Power Supply	V _{CC} =4.5V ~ 5.5V	V _{CC} =4.5V ~ 5.5V	V _{CC} =2.7V ~ 5.5V	AS6C62256-55PCN better
Operating Temperature	Commercial (0°C to 70°C)	Commercial (0°C to 70°C)	Commercial (0°C to 70°C)	Same
I/O Capacitance	CIO: 7pf (Max.)	CIO: 7pf (Max.)	CIO: 8pf (Max.)	Comparable
Read Cycle Time (tRC)	70ns (Min.)	70ns (Min.)	55ns (Min.)	AS6C62256-55PCN better
WriteCycleTime(tWC)	70ns (Min.)	70ns (Min.)	55ns (Min.)	AS6C62256-55PCN better
AddrAccessTime(tAA)	70ns (Max.)	70ns (Max.)	55ns (Max.)	AS6C62256-55PCN better
OE Access Time (tOE)	35ns (Max.)	35ns (Max.)	30ns (Max.)	Comparable
V_{OH}(V) @ -1.0mA	2.4 (Min.)	2.4 (Min.)	2.4 (Min.)	Same
V_{OL}(V)	0.4 (Max.)	0.4 (Max.)	0.4 (Max.)	Same
V_{IH}(V)	2.2 (Min.)	2.2 (Min.)	2.4 (Min.)	Comparable
V_{IL}(V)	0.8 (Max.)	0.6 (Max.)	0.6 (Max.)	Comparable
I_{LI} / I_{LO}(uA)	2 (Max.)	2 (Max.)	1 (Max.)	Comparable
Oper. Current	I _{CC} = 70mA(Max.)	I _{CC} = 70mA(Max.)	I _{CC} = 45mA(Max.)	AS6C62256-55PCN better
Standby Current I_{SB1} (CMOS level)	10uA (Max.)	5uA (Max.)	15uA (Max.)	Comparable
Standby Current I_{SB2} (TTL level)	1mA (Max.)	1mA (Max.)	3mA	Different
V_{DR}	2 (Min.)	2V (Min.)	1.5V (Min.)	AS6C62256-55PCN better
Package Dim	28Pin 600mil PDIP	28Pin 600mil PDIP	28Pin 600mil PDIP	Same
Package Material	Pb and Halogen Free	Pb and Halogen Free	Pb and Halogen Free	Same
Pin to Pin Compatible	Yes	Yes	Yes	Same